

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please replace paragraph [01] as follows:

[01] The present application is a divisional application under 37 C.F.R. §1.53(b) ~~of pending prior Application No. 10/166,685 filed on June 12, 2002 (now allowed)~~ of a prior Application No. 10/166,685 filed on June 12, 2002 which is now patent No. 6,667,228, the entire contents of which are hereby incorporated by reference. The present application also claims the benefit of Korean Patent Application No. P2001-32904 filed June 12, 2001, the entire contents of which are herein fully incorporated by reference.

Please replace paragraph [31] as follows:

[31] In another embodiment, instead of forming the first contact hole 27a after the first insulating interlayer 24 is deposited, a second insulating interlayer 26 is deposited on the first insulating interlayer 24 (without the first contact hole). Then the first insulating interlayer 24 and the second insulating interlayer 26 are removed selectively to expose a portion of the semiconductor substrate 21 corresponding to the impurity region and thereby form an extended contact hole corresponding to the first and second contact holes combined together. A silicon film such as a monosilicon or polysilicon film is then deposited on the entire surface of the semiconductor substrate 21 and buried in the extended contact hole. Then the silicon film formed on the second

insulating interlayer 26 and a portion of the silicon film buried in the extended contact hole are removed by an etch-back process or the like to form the first cell plug 25 and a contact hole (27b) on the first cell plug 25 through the second insulating interlayer 26.